

THYRISTOR MODULE (NON-ISOLATED TYPE)

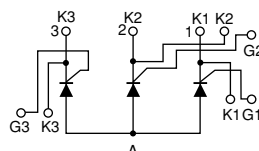
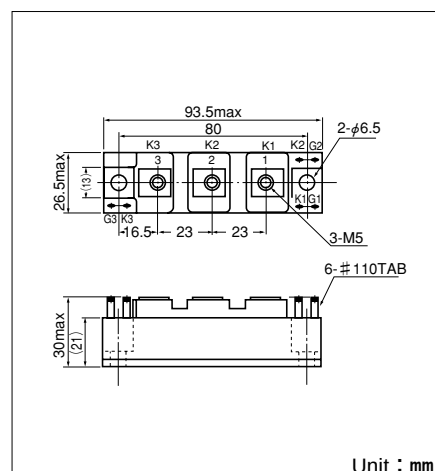
PWB100A

PWB100A is a Thyristor module suitable for low voltage, 3 phase rectifier applications.

- $I_{T(AV)}$ 100A (each device)
- High Surge Current 3500 A (60Hz)
- Easy Construction
- Non-isolated. Mounting base as common Anode terminal

(Applications)

Welding power Supply
Various DC power Supply



Maximum Ratings

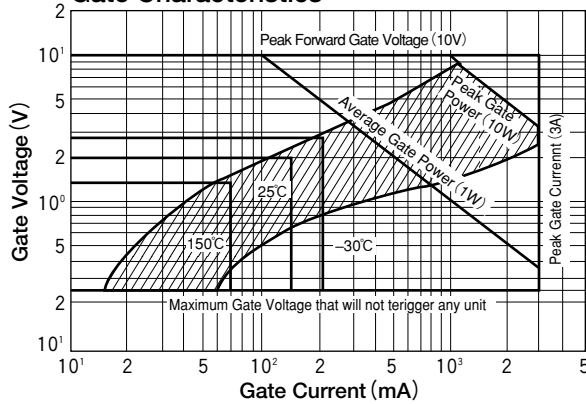
Symbol	Item	Ratings		Unit
		PWB100A30	PWB100A40	
VRRM	Repetitive Peak Reverse Voltage	300	400	V
VRSM	Non-Repetitive Peak Reverse Voltage	360	480	V
VDRM	Repetitive Peak Off-State Voltage	300	400	V

Symbol	Item		Conditions	Ratings	Unit
$I_{T(AV)}$	Average On-State Current		Single phase, half wave, 180° conduction, $T_c : 114^{\circ}\text{C}$	100	A
$I_{T(RMS)}$	R.M.S. On-State Current		Single phase, half wave, 180° conduction, $T_c : 114^{\circ}\text{C}$	157	A
I_{TSM}	Surge On-State Current		$\frac{1}{2}$ cycle, 50Hz/60Hz, peak value, non-repetitive	3200/3500	A
I^2t	I^2t			51000	A ² S
P_{GM}	Peak Gate Power Dissipation			10	W
$P_{G(AV)}$	Average Gate Power Dissipation			1	W
I_{FGM}	Peak Gate Current			3	A
V_{FGM}	Peak Gate Voltage (Forward)			10	V
V_{RGM}	Peak Gate Voltage (Reverse)			5	V
di/dt	Critical Rate of Rise of On-State Current		$I_G=200\text{mA}$, $T_j=25^{\circ}\text{C}$, $V_D=\frac{1}{2}V_{DRM}$, $dI_G/dt=1\text{A}/\mu\text{s}$	50	A/ μs
T_j	Operating Junction Temperature			-30 to +150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature			-30 to +125	$^{\circ}\text{C}$
	Mounting Torque	Mounting (M6)	Recommended Value 2.5-3.9 (25-40)	4.7 (48)	N·m (kgf·cm)
		Terminal (M5)	Recommended Value 1.5-2.5 (15-25)	2.7 (28)	
	Mass			170	g

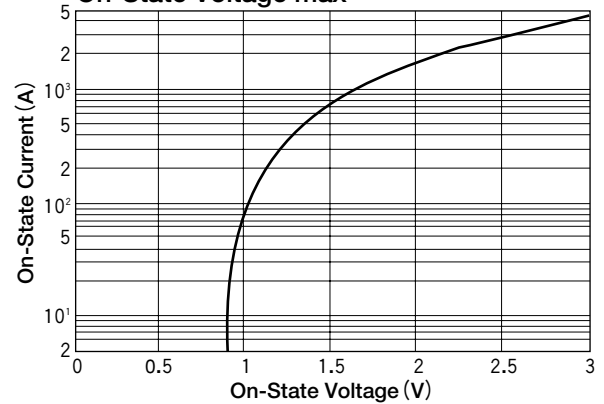
Electrical Characteristics

Symbol	Item		Conditions	Ratings	Unit
I_{DRM}	Repetitive Peak Off-State Current, max.		at V_{DRM} , single phase, half wave, $T_j=150^{\circ}\text{C}$	15	mA
I_{RRM}	Repetitive Peak Reverse Current, max.		at V_{DRM} , single phase, half wave, $T_j=150^{\circ}\text{C}$	15	mA
V_{TM}	Peak On-State Voltage, max.		On-State Current 310A, $T_j=25^{\circ}\text{C}$ Inst. measurement	1.20	V
I_{GT}/V_{GT}	Gate Trigger Current/Voltage, max.		$T_j=25^{\circ}\text{C}$, $I_T=1\text{A}$, $V_D=6\text{V}$	150/2	mA/V
V_{GD}	Non-Trigger Gate, Voltage. min.		$T_j=150^{\circ}\text{C}$, $V_D=\frac{1}{2}V_{DRM}$	0.25	V
t_{gt}	Turn On Time, max.		$I_T=100\text{A}$, $I_G=200\text{mA}$, $T_j=25^{\circ}\text{C}$, $V_D=\frac{1}{2}V_{DRM}$, $dI_G/dt=1\text{A}/\mu\text{s}$	10	μs
dv/dt	Critical Rate of Rise of Off-State Voltage, min.		$T_j=150^{\circ}\text{C}$, $V_D=\frac{2}{3}V_{DRM}$, Exponential wave.	50	V/ μs
I_H	Holding Current, typ.		$T_j=25^{\circ}\text{C}$	70	mA
$R_{th(j-c)}$	Thermal Impedance, max.		Junction to case ($\frac{1}{3}$ Module)	0.3	$^{\circ}\text{C}/\text{W}$

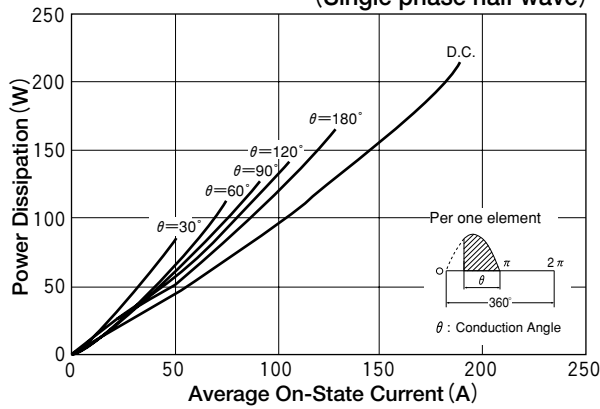
Gate Characteristics



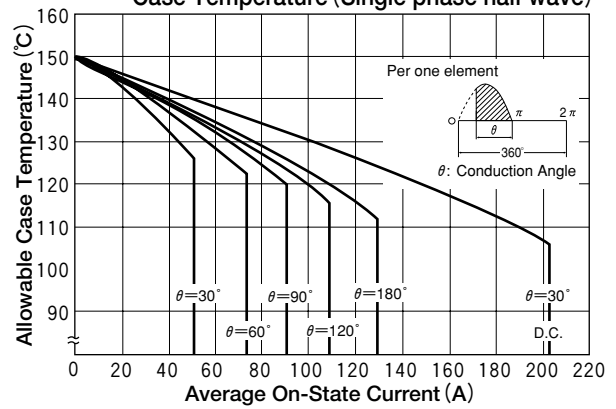
On-State Voltage max



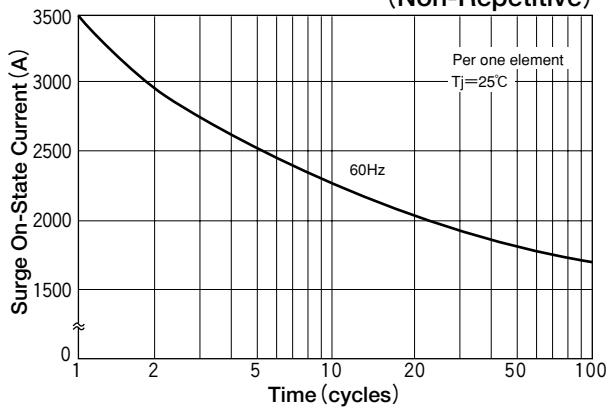
Average On-State Current Vs Power Dissipation (Single phase half wave)



Average On-State Current Vs Maximum Allowable Case Temperature (Single phase half wave)



Surge On-State Current Rating (Non-Repetitive)



Transient Thermal Impedance

